

# Dingkun Ren

## List of Publications by Year in descending order

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Version: 2024-02-01

21  
papers

250  
citations

1163117

8  
h-index

940533

16  
g-index

21  
all docs

21  
docs citations

21  
times ranked

415  
citing authors

#	ARTICLE	IF	CITATIONS
1	Mapping Charge Recombination and the Effect of Point-Defect Insertion in GaAs Nanowire Heterojunctions. <i>Physical Review Applied</i> , 2021, 16, .	3.8	1
2	Lateral carrier transfer for high density InGaAs/GaAs surface quantum dots. <i>Journal of Luminescence</i> , 2020, 218, 116870.	3.1	5
3	Self-assembly of tensile-strained Ge quantum dots on InAlAs(111)A. <i>Journal of Crystal Growth</i> , 2020, 533, 125468.	1.5	8
4	Significant suppression of surface leakage in GaSb/AlAsSb heterostructure with Al <sub>2</sub> O <sub>3</sub> passivation. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 090907.	1.5	3
5	Inducing Electrically-Active Defects in a Gallium Arsenide Nanowire with an Electron Beam. <i>Microscopy and Microanalysis</i> , 2019, 25, 1618-1619.	0.4	0
6	Room-Temperature Midwavelength Infrared InAsSb Nanowire Photodetector Arrays with Al <sub>2</sub> O <sub>3</sub> Passivation. <i>Nano Letters</i> , 2019, 19, 2793-2802.	9.1	52
7	Energy-sensitive GaSb/AlAsSb Separate Absorption and Multiplication Avalanche Photodiodes for X-ray and Gamma-ray Detection. <i>Advanced Optical Materials</i> , 2019, 7, 1900107.	7.3	5
8	Feasibility of achieving high detectivity at short- and mid-wavelength infrared using nanowire-plasmonic photodetectors with <i>pn</i> heterojunctions. <i>Nanotechnology</i> , 2019, 30, 044002.	2.6	9
9	InGaAs-GaAs Nanowire Avalanche Photodiodes Toward Single-Photon Detection in Free-Running Mode. <i>Nano Letters</i> , 2019, 19, 582-590.	9.1	40
10	High-efficiency ultrafast optical-to-electrical converters based on InAs nanowire-plasmonic arrays. <i>Optics Letters</i> , 2019, 44, 4666.	3.3	6
11	Exploring time-resolved photoluminescence for nanowires using a three-dimensional computational transient model. <i>Nanoscale</i> , 2018, 10, 7792-7802.	5.6	7
12	Catalyst-free selective-area epitaxy of GaAs nanowires by metal-organic chemical vapor deposition using triethylgallium. <i>Nanotechnology</i> , 2018, 29, 085601.	2.6	16
13	Uncooled Photodetector at Short-Wavelength Infrared Using InAs Nanowire Photoabsorbers on InP with <i>pn</i> Heterojunctions. <i>Nano Letters</i> , 2018, 18, 7901-7908.	9.1	35
14	A three-dimensional insight into correlation between carrier lifetime and surface recombination velocity for nanowires. <i>Nanotechnology</i> , 2018, 29, 504003.	2.6	5
15	Axial InAs(Sb) inserts in selective-area InAsP nanowires on InP for optoelectronics beyond 25 $\mu\text{m}$ . <i>Optical Materials Express</i> , 2018, 8, 1075.	3.0	12
16	Feasibility of Tracking Multiple Single-Cell Properties with Impedance Spectroscopy. <i>ACS Sensors</i> , 2018, 3, 1005-1015.	7.8	16
17	Feasibility of room-temperature mid-wavelength infrared photodetectors using InAsSb nanostructured photoabsorbers. , 2018, , .		2
18	Numerical analysis of nanowire surface recombination using a three-dimensional transient model. , 2018, , .		0

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19	Seeding layer assisted selective-area growth of As-rich InAsP nanowires on InP substrates. <i>Nanoscale</i> , 2017, 9, 8220-8228.	5.6	16
20	Selective-area InAsSb Nanowires on InP for 3-5 $\mu$ m Mid-wavelength Infrared Optoelectronics. <i>MRS Advances</i> , 2017, 2, 3565-3570.	0.9	7
21	Optical Characterization of AlAsSb Digital Alloy and Random Alloy on GaSb. <i>Crystals</i> , 2017, 7, 313.	2.2	5